

Detlef Hommel

List of Publications by Year in descending order

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604
papers

10,921
citations

50566

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64407

83
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docs citations

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times ranked

7574
citing authors

#	ARTICLE	IF	CITATIONS
1	Detailed surface studies on the reduction of Al incorporation into AlGa _N grown by molecular beam epitaxy in the Ga-droplet regime. <i>Vacuum</i> , 2022, 202, 111168.	1.6	4
2	Role of Temperature in Arsenic-Induced Antisurfactant Growth of GaN Microrods. <i>ACS Omega</i> , 2022, 7, 24777-24784.	1.6	0
3	X-ray diffraction studies of residual strain in AlN/sapphire templates. <i>Measurement: Journal of the International Measurement Confederation</i> , 2022, 200, 111611.	2.5	2
4	Arsenic-Induced Growth of Dodecagonal GaN Microrods with Stable <i>c</i> -Plane Walls. <i>Advanced Optical Materials</i> , 2021, 9, 2001348.	3.6	7
5	Improved-sensitivity integral SQUID magnetometry of (Ga,Mn)N thin films in proximity to Mg-doped GaN. <i>Journal of Alloys and Compounds</i> , 2021, 868, 159119.	2.8	8
6	Band engineering in nitrogen-rich AlGa _N As quaternary alloys. <i>Vacuum</i> , 2021, 189, 110240.	1.6	2
7	Growth and properties of the GaN cap layer strongly influenced by the composition of the underlying AlGa _N . <i>Materials Science in Semiconductor Processing</i> , 2021, 136, 106125.	1.9	3
8	Influence of pulsed Al deposition on quality of Al-rich Al(Ga)N structures grown by molecular beam epitaxy. <i>Surfaces and Interfaces</i> , 2021, 27, 101560.	1.5	2
9	Anisotropic thermal conductivity of AlGa _N /Ga _N superlattices. <i>Nanotechnology</i> , 2021, 32, 075707.	1.3	8
10	Raman scattering studies of the lateral Mn distribution in MBE-grown Ga _{1-x} Mn _x N epilayers. <i>Journal of Alloys and Compounds</i> , 2020, 817, 152789.	2.8	3
11	Bandgap engineering in III-nitrides with boron and group V elements: Toward applications in ultraviolet emitters. <i>Applied Physics Reviews</i> , 2020, 7, .	5.5	27
12	Boron influence on bandgap and photoluminescence in BGa _N grown on AlN. <i>Journal of Applied Physics</i> , 2020, 127, .	1.1	9
13	Determination of dislocation density in GaN/sapphire layers using XRD measurements carried out from the edge of the sample. <i>Journal of Alloys and Compounds</i> , 2020, 825, 153838.	2.8	20
14	Structural and electrical properties of Pd/p-GaN contacts for GaN-based laser diodes. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2020, 38, 032211.	0.6	1
15	Crystal field model simulations of magnetic response of pairs, triplets and quartets of Mn ³⁺ ions in GaN. <i>New Journal of Physics</i> , 2020, 22, 123016.	1.2	5
16	Surface studies of physicochemical properties of As films on GaN(0001). <i>Applied Surface Science</i> , 2019, 493, 384-388.	3.1	11
17	Electrical characteristics of vertical-geometry Schottky junction to magnetic insulator (Ga,Mn)N heteroepitaxially grown on sapphire. <i>Journal of Alloys and Compounds</i> , 2019, 804, 415-420.	2.8	3
18	As-related stability of the band gap temperature dependence in N-rich GaNAs. <i>Applied Physics Letters</i> , 2019, 115, 092106.	1.5	8

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19	XPS studies on the role of arsenic incorporated into GaN. <i>Vacuum</i> , 2019, 167, 73-76.	1.6	24
20	Material Gain Engineering in Staggered Polar AlGaN/AlN Quantum Wells Dedicated for Deep UV Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2019, 25, 1-8.	1.9	3
21	Verification of threading dislocations density estimation methods suitable for efficient structural characterization of Al _x Ga _{1-x} N/GaN heterostructures grown by MOVPE. <i>Journal of Applied Physics</i> , 2019, 126, 165304.	1.1	4
22	The Influence of Oxygen and Carbon Contaminants on the Valence Band of p-GaN(0001). <i>Acta Physica Polonica A</i> , 2019, 136, 585-588.	0.2	5
23	Infections tropicales graves dans les départements français d'Amérique, Antilles françaises et Guyane. <i>Medicine Intensive Reanimation</i> , 2019, 28, 202-216.	0.1	1
24	Modulated Ammonia Flow - Low Temperature AlN Buffer LP-MOVPE Growth for High Quality AlGaIn Layers. <i>Acta Physica Polonica A</i> , 2019, 136, 589-592.	0.2	0
25	Impact of substrate temperature on magnetic properties of plasma-assisted molecular beam epitaxy grown (Ga,Mn)N. <i>Journal of Alloys and Compounds</i> , 2018, 747, 946-959.	2.8	18
26	Emission and material gain spectra of polar compressive strained AlGaIn quantum wells grown on virtual AlGaIn substrates: Tuning emission wavelength and mixing TE and TM mode of light polarization. <i>Semiconductor Science and Technology</i> , 2018, 33, 075003.	1.0	5
27	Contactless electroreflectance study of the surface potential barrier in n-type and p-type InAlAs van Hoof structures lattice matched to InP. <i>Journal Physics D: Applied Physics</i> , 2018, 51, 215104.	1.3	4
28	Lonomia caterpillar envenoming in French Guiana reversed by the Brazilian antivenom: A successful case of international cooperation for a rare but deadly tropical hazard. <i>Toxicon</i> , 2018, 151, 74-78.	0.8	9
29	Fermi level and bands offsets determination in insulating (Ga,Mn)N/GaN structures. <i>Scientific Reports</i> , 2017, 7, 41877.	1.6	23
30	Emission dynamics of hybrid plasmonic gold/organic GaN nanorods. <i>Nanotechnology</i> , 2017, 28, 505710.	1.3	6
31	Polarization-dependent XAFS and density functional theory investigations of the quality of the epitaxial GaMnN structure. <i>Journal of Alloys and Compounds</i> , 2017, 725, 632-638.	2.8	8
32	The influence of the quantum-confined Stark effect on InGaIn/AlGaIn quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , 2017, 254, 1600325.	0.7	0
33	Influence of the sample design on the strong light-matter coupling in ZnSe-based periodic structures. <i>Journal of Physics: Conference Series</i> , 2017, 864, 012020.	0.3	0
34	Trap and non-trap dispersions in admittance spectra of hexagonal Galliumnitride. , 2017, , 359-362.		0
35	Exciton emission from plasmonic-organic-III-V-semiconductor nanowires and nanorods. , 2016, ,		0
36	Bragg polaritons in a ZnSe-based unfolded microcavity at elevated temperatures. <i>Applied Physics Letters</i> , 2016, 108, 121105.	1.5	3

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37	Composition analysis of coaxially grown InGaN multi quantum wells using scanning transmission electron microscopy. Journal of Applied Physics, 2016, 119, 175701.	1.1	0
38	Comparison of magneto-optical properties of various excitonic complexes in CdTe and CdSe self-assembled quantum dots. Journal of Physics Condensed Matter, 2016, 28, 265302.	0.7	8
39	Asymmetric skew X-ray diffraction at fixed incidence angle: application to semiconductor nano-objects. Journal of Applied Crystallography, 2016, 49, 961-967.	1.9	7
40	Observation of a hybrid state of Tamm plasmons and microcavity exciton polaritons. Scientific Reports, 2016, 6, 34392.	1.6	27
41	Tamm plasmon polaritons in the visible spectral region and its optical properties in ZnSe-based microcavities. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 498-502.	0.8	1
42	Polarity dependence of Mn incorporation in (Ga,Mn)N superlattices. Journal of Crystal Growth, 2016, 437, 49-52.	0.7	1
43	Nitride Semiconductors. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 897-897.	0.8	0
44	Nitride Semiconductors. Physica Status Solidi (B): Basic Research, 2015, 252, 853-853.	0.7	0
45	The electronic structure of homogeneous ferromagnetic (Ga, Mn)N epitaxial films. Journal of Applied Physics, 2015, 117, .	1.1	11
46	Exciton-Polariton Gas as a Nonequilibrium Coolant. Physical Review Letters, 2015, 114, 186403.	2.9	25
47	Tailoring the optical properties of wide-bandgap based microcavities via metal films. Applied Physics Letters, 2015, 107, .	1.5	8
48	Polariton lasing in high-quality selenide-based micropillars in the strong coupling regime. Applied Physics Letters, 2015, 107, .	1.5	15
49	Determination of the Fermi level position in dilute magnetic Ga _{1-x} Mn _x N films. Journal of Applied Physics, 2014, 115, 123706.	1.1	6
50	Surface oxidation of GaN(0001): Nitrogen plasma-assisted cleaning for ultrahigh vacuum applications. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, 051401.	0.9	11
51	Fabrication of ZnSe-based microcavities for lasing in the strong coupling regime and polariton confinement. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1267-1272.	0.8	0
52	Electrically driven single photon emission from a CdSe/ZnSSe/MgS semiconductor quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1256-1259.	0.8	7
53	GaN tubes with coaxial non-polar and semipolar GaInN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 648-651.	0.8	6
54	Electrically driven single photon emission from a CdSe/ZnSSe single quantum dot at 200 K. Applied Physics Letters, 2014, 105, .	1.5	7

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55	Micropillar Cavity Containing a CdTe Quantum Dot with a Single Manganese Ion. Crystal Growth and Design, 2014, 14, 988-992.	1.4	23
56	Inhibition and Enhancement of the Spontaneous Emission of Quantum Dots in Micropillar Cavities with Radial-Distributed Bragg Reflectors. ACS Nano, 2014, 8, 9970-9978.	7.3	30
57	Colour and multicolour tuning of InGaN quantum dot based light-emitting diodes. Journal Physics D: Applied Physics, 2014, 47, 055108.	1.3	3
58	Influence of a low-temperature capping on the crystalline structure and morphology of InGaN quantum dot structures. Journal of Alloys and Compounds, 2014, 585, 572-579.	2.8	5
59	Photonic Crystal Structures Based on GaN Ultrathin Membranes. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 271-275.	0.1	5
60	Influence of Static Atomic Displacements on Composition Quantification of AlGaIn/GaN Heterostructures from HAADF-STEM Images. Microscopy and Microanalysis, 2014, 20, 1463-1470.	0.2	11
61	Growth of AlN by pulsed and conventional MOVPE. Journal of Crystal Growth, 2013, 381, 100-106.	0.7	15
62	Phase diagram and critical behavior of the random ferromagnet $\text{Ga}_{1-x}\text{Mn}_x$. Physical Review B, 2013, 88, .	1.5	53
63	On the structural properties of MgS-rich II-VI-based microcavities. Journal of Crystal Growth, 2013, 378, 270-273.	0.7	3
64	Nitride based heterostructures with Ga- and N-polarity for sensing applications. Journal of Crystal Growth, 2013, 370, 68-73.	0.7	11
65	Trap levels in the atomic layer deposition-ZnO/GaN heterojunction Thermal admittance spectroscopy studies. Journal of Applied Physics, 2013, 113, .	1.1	9
66	Light-matter coupling in ZnTe-based micropillar cavities containing CdTe quantum dots. Journal of Applied Physics, 2013, 113, 136504.	1.1	9
67	The impact of nanoporation on persistent photoconductivity and optical quenching effects in suspended GaN nanomembranes. Applied Physics Letters, 2013, 103, 243113.	1.5	3
68	Blue lasing and strong coupling in ZnSe monolithic microcavities. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1230-1233.	0.8	1
69	Growth of II-VI and III-nitride quantum-dot microcavity systems. , 2012, , 447-484.		1
70	Single photon emission from InGaIn/GaN quantum dots up to 50%K. Applied Physics Letters, 2012, 100, .	1.5	39
71	Strong coupling in monolithic microcavities with ZnSe quantum wells. Applied Physics Letters, 2012, 100, 161104.	1.5	23
72	Blue monolithic II-VI-based vertical-cavity surface-emitting laser. Applied Physics Letters, 2012, 100, 121102.	1.5	6

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73	Pronounced Purcell enhancement of spontaneous emission in CdTe/ZnTe quantum dots embedded in micropillar cavities. Applied Physics Letters, 2012, 101, 132105.	1.5	21
74	Complementary information on CdSe/ZnSe quantum dot local structure from extended X-ray absorption fine structure and diffraction anomalous fine structure measurements. Journal of Alloys and Compounds, 2012, 523, 155-160.	2.8	13
75	Ga α xMn α xN epitaxial films with high magnetization. Applied Physics Letters, 2012, 101, .	1.5	48
76	Room temperature single photon emission from an epitaxially grown quantum dot. Applied Physics Letters, 2012, 100, 061114.	1.5	58
77	Strong phase separation of strained In α xMn α xN quantum dots. Applied Physics Letters, 2012, 100, 061114.	1.1	66
78	Optical Properties of InGaN Quantum Dots in Monolithic Pillar Microcavities. , 2011, , .		0
79	Composition mapping in InGaN by scanning transmission electron microscopy. Ultramicroscopy, 2011, 111, 1316-1327.	0.8	156
80	Far field emission of micropillar and planar microcavities lattice-matched to ZnTe. Open Physics, 2011, 9, 428-431.	0.8	7
81	Optical polariton properties in ZnSe-based planar and pillar structured microcavities. European Physical Journal B, 2011, 84, 381-384.	0.6	8
82	Properties of monolithic InGaN quantum dot pillar microcavities. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1573-1575.	0.8	0
83	Mg and Si dopant incorporation and segregation in GaN. Physica Status Solidi (B): Basic Research, 2011, 248, 1810-1821.	0.7	8
84	Cleaning and growth morphology of GaN and InGaN surfaces. Physica Status Solidi (B): Basic Research, 2011, 248, 1800-1809.	0.7	13
85	Microphotoluminescence studies on GaN-based airpost pillar microcavities containing InGaN quantum wells and quantum dots. Physica Status Solidi (B): Basic Research, 2011, 248, 1756-1764.	0.7	2
86	Catalyst free self-organized grown high-quality GaN nanorods. Physica Status Solidi (B): Basic Research, 2011, 248, 1787-1799.	0.7	4
87	Influence of growth imperfections on optical properties of nitride pillar VCSEL microcavities. Physica Status Solidi (B): Basic Research, 2011, 248, 1867-1870.	0.7	1
88	InGaN quantum dot growth in the limits of Stranski-Krastanov and spinodal decomposition. Physica Status Solidi (B): Basic Research, 2011, 248, 1765-1776.	0.7	30
89	Growth and characterization of nitride-based distributed Bragg reflectors. Physica Status Solidi (B): Basic Research, 2011, 248, 1748-1755.	0.7	20
90	Microstructural and compositional analyses of GaN-based nanostructures. Physica Status Solidi (B): Basic Research, 2011, 248, 1822-1836.	0.7	4

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91	Optical properties of wide-bandgap monolithic pillar microcavities with different geometries. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1246-1249.	0.8	1
92	Electroluminescence from InGaN quantum dots in a fully monolithic GaN/AlInN cavity. <i>Journal of Crystal Growth</i> , 2011, 320, 28-31.	0.7	5
93	Monolithic ZnTe-based pillar microcavities containing CdTe quantum dots. <i>Nanotechnology</i> , 2011, 22, 285204.	1.3	12
94	Light-emitting diode based on mask- and catalyst-free grown N-polar GaN nanorods. <i>Nanotechnology</i> , 2011, 22, 265202.	1.3	9
95	Cleaning of GaN(2 $\bar{1}10$) surfaces. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2011, 29, .	0.9	9
96	Optical Properties of CdTe QDs Formed Using Zn Induced Reorganization. <i>Acta Physica Polonica A</i> , 2011, 119, 627-629.	0.2	10
97	Toward Better Light-Confinement in Micropillar Cavities. <i>Acta Physica Polonica A</i> , 2011, 120, 877-879.	0.2	5
98	Epitaxial ZnO Films Grown at Low Temperature for Novel Electronic Application. <i>Acta Physica Polonica A</i> , 2011, 120, A-7-A-10.	0.2	8
99	Deep Levels Induced by CdTe/ZnTe Quantum Dots. <i>Acta Physica Polonica A</i> , 2011, 119, 630-632.	0.2	0
100	Manipulating the optical properties of CdSe/ZnSSe quantum dot based monolithic pillar microcavities. <i>Journal of Physics: Conference Series</i> , 2010, 210, 012006.	0.3	0
101	Mapping strain gradients in the FIB-structured InGaN/GaN multilayered films with 3D X-ray microbeam. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2010, 528, 52-57.	2.6	4
102	Electroluminescence from isolated single indium gallium nitride quantum dots up to 150%K. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010, 207, 1428-1430.	0.8	1
103	Excitons in motion in II-VI semiconductors. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 1521-1527.	0.7	11
104	Methods to spectrally tune II-VI-based monolithic microcavities. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 1539-1542.	0.7	0
105	Radiative recombination dynamics of CdSe/Zn(S,Se)/MgS quantum dots up to room temperature. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 1413-1415.	0.7	2
106	Mg-related acceptors in GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 1850-1852.	0.8	11
107	Influence of doping on optical properties of catalyst- and mask-free grown gallium nitride nanorods. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 2240-2242.	0.8	3
108	Temperature dependence of radiative recombination in CdSe quantum dots with enhanced confinement. <i>JETP Letters</i> , 2010, 92, 57-62.	0.4	0

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109	Electroluminescence from a Single Self-Assembled CdSe Quantum Dot. , 2010, , .		0
110	Radiative recombination in photoexcited quantum dots up to room temperature: The role of fine-structure effects. Physical Review B, 2010, 81, .	1.1	4
111	Optical and structural characterization of AlInN layers for optoelectronic applications. Journal of Applied Physics, 2010, 108, .	1.1	57
112	Optical bandpass switching by modulating a microcavity using ultrafast acoustics. Physical Review B, 2010, 81, .	1.1	29
113	Electroluminescence from a single InGaN quantum dot in the green spectral region up to 150 K. Nanotechnology, 2010, 21, 015204.	1.3	25
114	Polarized light emission from CdSe/ZnSSe quantum-dot monolithic pillar microcavities. Journal of Physics: Conference Series, 2010, 245, 012058.	0.3	1
115	Band gap bowing of binary alloys: Experimental results compared to theoretical tight-binding supercell calculations for $\langle \text{Cd} \rangle$. Physical Review B, 2010, 82, .	1.1	26
116	TEM characterization of catalyst- and mask-free grown GaN nanorods. Journal of Physics: Conference Series, 2010, 209, 012020.	0.3	8
117	Optical properties of InGaN quantum dots in monolithic pillar microcavities. Applied Physics Letters, 2010, 96, 251906.	1.5	9
118	Motion-enhanced magnetic moments of excitons in ZnSe. Physical Review B, 2010, 81, .	1.1	12
119	High-reflectivity broadband distributed Bragg reflector lattice matched to ZnTe. Applied Physics Letters, 2009, 94, 191108.	1.5	32
120	A CdSe quantum dot based resonant cavity light-emitting diode showing single line emission up to 90 K. Nanotechnology, 2009, 20, 015401.	1.3	7
121	Emission properties of ZnSe-based pillar microcavities at elevated temperatures. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 508-511.	0.8	2
122	Electric field-induced exciton localization in quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 551-555.	0.8	7
123	Influence of piezoelectric fields on excitonic complexes in InGaN quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 872-875.	0.8	3
124	Transmission electron microscopical investigation of AlGaIn/GaN distributed Bragg reflectors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S680.	0.8	3
125	Oxide removal from GaN(0001) surfaces. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S305.	0.8	11
126	Improved capping layer growth towards increased stability of InGaIn quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S561-S564.	0.8	16

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127	Optical properties of GaN nanorods grown catalyst-free on r-plane sapphire. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S578.	0.8	5
128	Optical properties and modal gain of InGaN quantum dot stacks. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S590-S593.	0.8	5
129	Low-temperature growth of InGaN/GaN nano-islands investigated by grazing-incidence X-ray diffraction. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S602.	0.8	1
130	Incorporation of QD ensembles in separate confinement heterostructures for long wavelength emission. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S921-S924.	0.8	0
131	Local structure of uncapped and capped InGaN/GaN quantum dots. Journal of Synchrotron Radiation, 2009, 16, 494-497.	1.0	1
132	Atomic structure of the non-polar GaN(110) surface by cross-sectional scanning tunneling microscopy. Physica Status Solidi - Rapid Research Letters, 2009, 3, 91-93.	1.2	14
133	Temperature dependence of the thermal expansion of AlN. Applied Physics Letters, 2009, 94, .	1.5	83
134	Highly ordered catalyst-free and mask-free GaN nanorods on r-plane sapphire. Nanotechnology, 2009, 20, 075604.	1.3	26
135	Electrically driven room temperature operation of a single quantum dot emitter. , 2009, , .		1
136	Optical Study of ZnTe-Based 2D and 0D Photonic Structures Containing CdTe/ZnTe Quantum Dots. Acta Physica Polonica A, 2009, 116, 888-889.	0.2	7
137	Direct MOVPE- and MBE-growth of a-plane GaN on r-plane sapphire. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1836-1838.	0.8	8
138	Distributed Bragg reflectors in comparison to RUGATE and nested super lattices - growth, reflectivity, and conductivity. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1839-1842.	0.8	4
139	Integration of InGaN quantum dots into nitride-based microcavities. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2320-2322.	0.8	8
140	Optical properties of single and multi-layer InGaN quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1883-1885.	0.8	5
141	Absorption and emission of polariton modes in a ZnSe/ZnSSe heterostructure. Physica Status Solidi (B): Basic Research, 2008, 245, 1093-1097.	0.7	6
142	Structural investigation of growth and dissolution of nano-islands grown by molecular beam epitaxy. Journal of Crystal Growth, 2008, 310, 748-756.	0.7	7
143	Strain compensated AlGaIn/GaN-Bragg-reflectors with high Al content grown by MOVPE. Journal of Crystal Growth, 2008, 310, 4923-4926.	0.7	10
144	Room temperature emission from CdSe single quantum dots embedded in high bandgap barrier material. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1938-1940.	1.3	3

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145	Green laser emission from monolithic II-VI-based pillar microcavities near room temperature. Applied Physics Letters, 2008, 92, 031101.	1.5	23
146	Wide-Bandgap Quantum Dot Based Microcavity VCSEL Structures. , 2008, , 29-41.		2
147	Electrically driven single quantum dot emitter operating at room temperature. Applied Physics Letters, 2008, 93, .	1.5	20
148	Fine tuning of quantum-dot pillar microcavities by focused ion beam milling. Applied Physics Letters, 2008, 92, .	1.5	19
149	Determination of the Temperature Dependent Thermal Expansion Coefficients of Bulk AlN by HRXRD. Acta Physica Polonica A, 2008, 114, 1193-1200.	0.2	38
150	Properties and Prospects of ZnSe-Based Quantum Dot Microcavity VCSEL Structures. Journal of the Korean Physical Society, 2008, 53, 83-87.	0.3	2
151	In situ observation of Zn-induced etching during CdSe quantum dot formation using time-resolved ellipsometry. Applied Physics Letters, 2007, 90, 221102.	1.5	7
152	Interfacial structure of a-plane GaN grown on r-plane sapphire. Applied Physics Letters, 2007, 90, 081918.	1.5	15
153	Room temperature emission from CdSe/ZnSSe/MgS single quantum dots. Applied Physics Letters, 2007, 90, 101114.	1.5	41
154	Coherent exciton-LO-phonon polarons in ZnSe quantum wells with strong confinement. Physical Review B, 2007, 75, .	1.1	2
155	Spatially Resolved Characterization of Plastic Deformation Induced by Focused-Ion Beam Processing in Structured InGaN/GaN Layers. Materials Research Society Symposia Proceedings, 2007, 1020, 1.	0.1	0
156	InGaN Selfassembled Quantum Dots Investigated By X-Ray Diffraction-Anomalous-Fine Structure Technique. AIP Conference Proceedings, 2007, , .	0.3	2
157	Concentration Measurement In Free-Standing InGaN Nano-Islands With Transmission Electron Microscopy. Microscopy and Microanalysis, 2007, 13, 312-313.	0.2	3
158	Effect of sapphire-substrate thickness on the curvature of thick GaN films grown by hydride vapor phase epitaxy. Journal of Applied Physics, 2007, 102, 123507.	1.1	9
159	Dengue s'vire avec d'effaillance multivisc'ale. JEUR/Journal Europ'een Des Urgences, 2007, 20, 158-160. 0.0		0
160	Anisotropic strain and phonon deformation potentials in GaN. Physical Review B, 2007, 75, .	1.1	99
161	Metastability of the UV luminescence in Mg-doped GaN layers grown by MOVPE on quasi-bulk GaN templates. Physica B: Condensed Matter, 2007, 401-402, 302-306.	1.3	6
162	Investigation of CdSe quantum dots in MgS barriers as active region in light emitting diodes. Journal of Crystal Growth, 2007, 301-302, 789-792.	0.7	13

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163	Deep ridge GaN cw-laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 78-81.	0.8	6
164	Homoepitaxial laser diodes emitting at 390 nm and the influence of substrate quality. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 74-77.	0.8	0
165	Phonons in strained AlGaIn/GaN superlattices. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 170-174.	0.8	5
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